

HSB276AYP

Silicon Schottky Barrier Diode for High Speed Switching

HITACHI

ADE-208-1051 (Z)

Rev.0

Jan. 2001

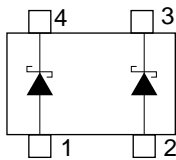
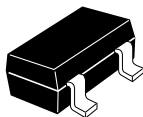
Features

- High forward current, Low capacitance.
- CMPAK - 4 Package is suitable for high density surface mounting and high speed assembly.

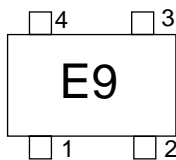
Ordering Information

Type No.	Laser Mark	Package Code
HSB276AYP	E9	CMPAK- 4

Outline



(Top View)



(Top View)

1. Anode
2. Anode
3. Cathode
4. Cathode

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	5	V
Reverse voltage	V_R	3	V
Average rectified current	I_O^*	30	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note: Per one device

Electrical Characteristics ($T_a = 25^\circ\text{C}$) *²

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3	—	—	V	$I_R = 1\text{ mA}$
Reverse current	I_R	—	—	50	μA	$V_R = 0.5\text{ V}$
Forward current	I_F	35	—	—	mA	$V_F = 0.5\text{ V}$
Capacitance	C	—	—	0.85	pF	$V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$
Capacitance deviation	ΔC	—	—	0.10	pF	$V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$
ESD-Capability * ¹	—	30	—	—	V	$C = 200\text{ pF}$, $R = 0\ \Omega$ Both forward and reverse direction 1 pulse.

Notes: 1. Failure criterion ; $I_R > 100\ \mu\text{A}$ at $V_R = 0.5\text{ V}$

2. Per one device

Main Characteristic

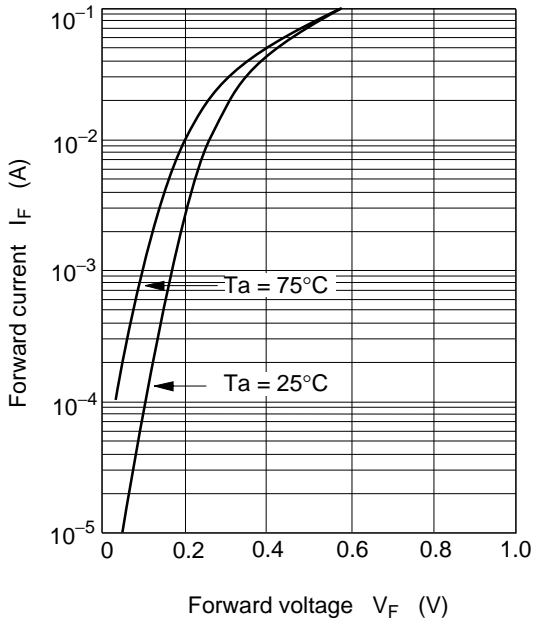


Fig.1 Forward current Vs. Forward voltage

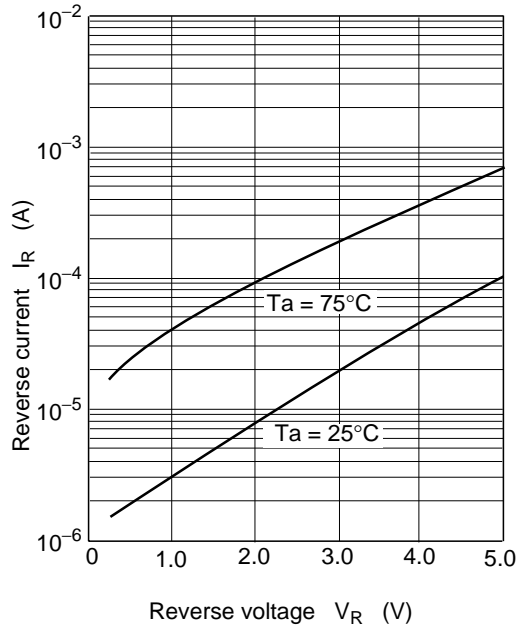


Fig.2 Reverse current Vs. Reverse voltage

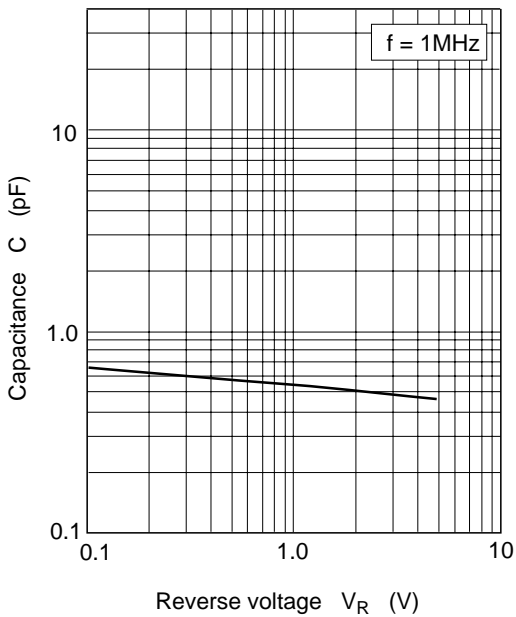
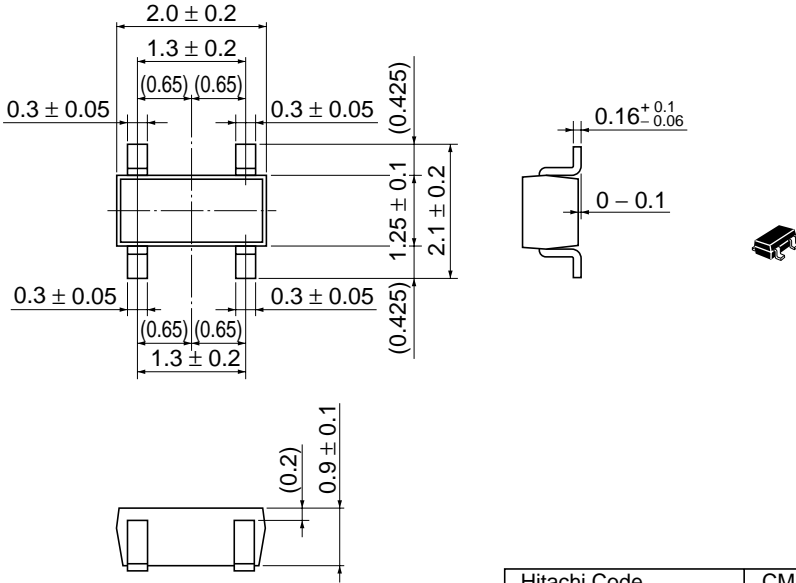


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



Hitachi Code	CMPAK-4(D)
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.006 g

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